

05-28-2002

RE



9/28/01

TO THE ASSISTANT COMMISSIONER FOR P.A.

102101707

uments or copy thereof.

1. Name of conveying party(ies): (If multiple assignors, list numerically)

Honeywell International, Inc.

Additional name(s) of conveying party(ies) attached?

( ) Yes (X) No

2. Name and address of receiving party(ies):

Name: Micron Technology, Inc.

Internal Address: P.O. Box 6

Street Address: 8000 South Federal Way

City: Boise State: Idaho ZIP: 83707-0006

Additional name(s) of receiving party(ies) attached?

( ) Yes (X) No

3. Nature of conveyance:

- (x) Assignment - Nunc Pro Tunc  
( ) Merger  
( ) Security Agreement  
( ) Change of Name  
( ) Other:

09388 673

Execution Date: (If multiple assignors, list execution dates in numerical order corresponding to numbers indicated in 1 above) December 18, 2000

4. Application number(s) or Patent number(s):

( ) Application(s) filed herewith Execution Date(s):

(x) Patent Application No.: See ATTACHMENT A  
Filing Date: See ATTACHMENT A

(x) Patent No.: See ATTACHMENT B  
Issue Date: See ATTACHMENT B

Additional numbers attached? ( ) Yes (X) No

5. Name and address of party to whom correspondence concerning document should be mailed:

Name: Adeel S. Akhtar  
KNOBBE, MARTENS, OLSON & BEAR, LLP  
Customer No. 20,995

Internal Address: Sixteenth Floor  
Street Address: 620 Newport Center Drive  
City: Newport Beach State: CA ZIP: 92660  
Attorney's Docket No.: MICRON.173GEN

7. Total fee (37 CFR 1.21(h)): \$1,360

(X) Enclosed

( ) Authorized to be charged to deposit account

8. Deposit account number: 11-1410

Please charge this account for any additional fees which may be required, or credit any overpayment to this account.

6. Total number of applications and patents involved: 34

9. Statement and signature.

To the best of my knowledge and belief, the foregoing information is true and correct, and any attached copy is a true copy of the original document.

Adeel S. Akhtar  
Name of Person Signing

*Adeel S. Akhtar*  
Signature

*See Pat.*  
September 25, 2001  
Date

Registration No. 41,394

Total number of pages including cover sheet, attachments and document: 8

Mail documents to be recorded with required cover sheet information to:

10/01/2001 JJALLAH2 00000010 09318073

01 FC:581

1360.00 00

RECORDPA  
W:\DOCS\ASA\ASA-10109.DOC 092501

U.S. Patent and Trademark Office  
Attn: Assignment Division  
Crystal Gateway-4  
1213 Jefferson Davis Highway, Suite 320  
Arlington, VA 22202

PATENT  
REEL: 012735 FRAME: 0417

**ATTACHMENT A**  
**PENDING PATENTS**

<b>Serial No.</b>	<b>Filing Date</b>	<b>Title</b>	<b>Former Docket No.</b>	<b>Docket No. (Client No.)</b>
09/318,073	5/25/99	Local Shielding for Memory Cells	25561	MICRON.196CP1
09/618,237	7/18/00	Magneto-Resistive Memory Array	26090	MICRON.211A
09/618,256	7/17/00	Magneto-Resistive Memory Having Sense Amplifier with Offset Control	26310	MICRON.210A
09/618,492	7/18/00	Memory Redundancy with programmable Non-Volatile Control	26083	MICRON.212A
09/618,504	7/18/00	MRAM Architectures for Increased Write Selectivity	25562	MICRON.198A
09/638,415	8/14/00	Magneto-Resistive Memory with Shared Wordline and Sense Line	26091	MICRON.213A
09/638,419	8/14/00	Passivated Magneto-Resistive Bit Structure and Passivation Method Therefor	25637	MICRON.214A
09/638,637	8/14/00	Pulsed Write Techniques for Magneto-Resistive Memories	26025	MICRON.215A
09/668,922	9/25/00	Shielding Arrangement to Protect A Circuit From Stray Magnetic Fields	26347	MICRON.216A

W:\DOCS\ASA\ASA-10082.DOC  
092001

Patent No.	Issue Date	Title	Former Docket No.	Docket No. (Client No.)
5,939,772	8/17/99	Shielded Package for Magnetic Devices	17179	MICRON.197A
5,956,267	9/21/99	Self-Aligned Wordline Keeper and Method of Manufacture Therefor	17079	MICRON.196A formerly 201A
5,982,658	11/9/99	MRAM Design to Reduce Dissimilar Nearest Neighbor Effects	16578	MICRON.208A
6,027,948	2/22/00	Method to Permit high Temperature Assembly Processes for Magnetically Sensitive Devices	17037	MICRON.207A
6,048,739	4/11/00	Method of Manufacturing a High Density Magnetic Memory Device	17078	MICRON.209A
6,134,138	10/17/00	Method and Apparatus for Reading a Magnetoresistive Memory	25598	MICRON.206A
6,147,922	11/14/00	Non-Volatile Storage Latch	17156A1	MICRON.185DV1
6,175,525	1/16/01	Non-Volatile Storage Latch	17156B1	MICRON.185CP1
6,178,111	1/23/01	Method and Apparatus for Writing Data States to Non-Volatile Storage Devices	25563	MICRON.199A
6,269,027	7/31/01	Non-Volatile Storage Latch	17156/25629	MICRON.185A

**ATTACHMENT B  
ISSUED PATENTS**

Patent No.	Issue Date	Title	Former Docket No.	Docket No. (Client No.)
4,731,757	3/15/88	Magnetoresistive Memory Including Thin Film Storage Cells Having Tapered Ends	10790	MICRON.189A
4,751,677	6/14/88	Differential Arrangement Magnetic Memory Cell	11874	MICRON.187A
4,754,431	6/28/88	Vialess Shorting Bars for Magnetoresistive Devices	12062	MICRON.195A
4,780,848	10/25/88	Magnetoresistive Memory with Multi-Layer Storage Cells Having layers of Limited Thickness	10789	MICRON.188A
4,829,476	5/9/89	Differential Magnetoresistive Memory Sensing	12056	MICRON.186A
4,897,288	1/30/90	Vialess Shorting Bars for Magnetoresistive Devices	12724	MICRON.192DV1
4,918,655	4/17/90	Magnetic Device Integrated Circuit Interconnection System	12092	MICRON.194A
4,953,002	8/28/90	Semiconductor Device Housing with Magnetic Field Protection	12035	MICRON.203FW1
5,012,444	4/30/91	Opposed Field Magnetoresistive Memory Sensing	13117	MICRON.191A
5,060,193	10/22/91	Magnetic State Entry Assurance	13268	MICRON.190A
5,064,499	11/12/91	Inductively Sensed Magnetic Memory	12173	MICRON.193A
5,349,302	9/20/94	Sense Amplifier Input Stage for Single Array Memory	13490	MICRON.202A
5,496,759	3/5/96	Highly Productive Magnetoresistive RAM Process	15742	MICRON.204A
5,569,617	10/29/96	Integrated Spacer for Magnetoresistive RAM	16139	MICRON.205A
5,756,366	5/26/98	Magnetic hardening of Bit Edges of Magnetoresistive RAM	16251	MICRON.200A


NUNC PRO TUNC ASSIGNMENT

Effective as of December 18, 2000, Honeywell International Inc., a Delaware corporation, acting through its Solid State Electronics Center having a principal place of business at 12001 State Hwy 55, Plymouth, Minnesota, and Honeywell Intellectual Properties Inc., an Arizona corporation having a principal place of business at 8440 South Hardy Dr., Tempe, Arizona (collectively referred to as "Honeywell") hereby make the following assignments for good and valuable consideration to Micron Technology Inc., a Delaware corporation having a principal place of business at 8000 S. Federal Way, Boise, Idaho: all right, title, and interest in the patents and patent applications listed in Appendix A and any of their related continuation, continuation-in-part, divisional or reissue applications or patents and any foreign counterpart applications or patents which now exist or which may later exist.

MICRON TECHNOLOGY, INC.

Signature: Printed Name: David S. HorvathTitle: Chief Patent Counsel

HONEYWELL INTERNATIONAL, INC.

Signature: Printed Name: DAVID S. HORVATHTitle: Chief Patent CounselHONEYWELL INTELLECTUAL  
PROPERTIES, INCSignature: Printed Name: KEITH ADAMSTitle: DIRECTOR - LICENSING

Appendix A

*Appendix*  
**SCHEDULE A (2 pages)**

SSEC MRAM Intellectual Property					
Patent Number	Title	First Inventor	Issue Date	Countries Filled	
Issued Patents					
4,731,757	MAGNETIC MEMORY CONFIGURATION	HUANG, J. S. T.	3/15/88	Japan/US	
4,751,877	HIGH SPEED MR MEMORY	DAUGHTON, J. M.	6/14/88	Japan/US	
4,789,048	MAGNETORESISTIVE MEMORY WITH MULTI-LAYER STORAGE CELLS HAVING LAYERS OF LIMITED THICKNESS	DAUGHTON, J. M.	10/25/88	US/EP/Netherlands/Japan/Great Britain/Germany/France/Italy/Canada	
4,829,476	A DIFFERENTIAL CIRCUIT ARCHITECTURE FOR A MAGNETO-RESISTIVE MEMORY	HANAWALT, R. E.	5/9/1989	US	
4,897,288	VIALESS SHORTING BARS FOR MAGNETORESISTIVE DEVICES	JENSON, M. L.	1/30/90	US	
4,918,655	COMPOSITE IC METALLURGY AND MAGNETIC SANDWICH FOR INTERCONNECTIONS	DAUGHTON, J. M.	4/17/90	US/Netherlands/Japan/Germany/Great Britain/France/Canada/EP	
5,012,444	OPPOSED FIELD MAGNETORESISTIVE MEMORY SENSING	HURST, Allan T.	4/30/91	US/Netherlands/Japan/Germany/Great Britain/France/Canada/EP	
5,060,193	MAGNETIC STATE ENTRY ASSURANCE	DAUGHTON, J. M.	10/22/91	US/Netherlands/Japan/Germany/Great Britain/France/Canada/EP	
5,064,490	INDUCTIVELY SENSED MAGNETIC MEMORY MANUFACTURING METHOD (AS AMENDED)	FRYER, R. B.	11/12/91	US	
5,349,302	SENSE AMPLIFIER INPUT STAGE FOR SINGLE ARRAY MEMORY	COOPER, L. K.	9/20/94	US	
5,496,759	HIGHLY PRODUCIBLE MRAM PROCESS	CHEN, H. J.	3/5/96	US	
5,569,617	INTEGRATED SPACER FOR MAGNETORESISTIVE RAM	BERG, Lonny L.	10/29/96	USA/PCT	
5,756,366	MAGNETIC HARDENING OF BIT EDGES OF MAGNETORESISTIVE RAM	BERG, Lonny L.	5/26/98	USA/PCT	
5,956,267	SELF-ALIGNED WORDLINE KEEPER AND METHOD OF MANUFACTURE THEREFOR	HURST, A.	9/21/99	US	
5,982,658	MRAM DESIGN TO REDUCE DISSIMILAR NEAREST NEIGHBOR EFFECTS	BERG, Lonny L.	11/9/99	US	
6,027,948	METHOD AND APPARATUS TO PERMIT HIGH TEMPERATURE ASSEMBLY PROCESSES FOR MAGNETICALLY SENSITIVE DEVICES	HURST, A.	2/2/00	US	
6,048,739	METHOD OF MANUFACTURING A HIGH DENSITY MAGNETIC MEMORY DEVICE	HURST, Allan T.	4/11/00	US	
4,953,002	SEMICONDUCTOR DEVICE HOUSING WITH MAGNETIC FIELD PROTECTION	KAWAI, T.	8/28/90	US	
4,754,431	VIALESS SHORTING BARS FOR MAGNETORESISTIVE DEVICES	JENSON, M. L.	6/28/88	US/EP/Netherlands/Japan/Great Britain/Germany/France	
5,939,772	SHIELDED PACKAGE FOR MAGNETIC DEVICES	HURST, Allan T.	8/17/99	US	

<b>Pending Patent Applications</b>					
Docket Number	Title	First Inventor	Filing Date	Countries Filed	
25561	LOCAL SHIELDING FOR MEMORY CELLS	SATHER, Jeffrey Scott	5/25/99	US/PCT/Taiwan	
25582	MRAM ARCHITECTURES FOR INCREASED WRITE SELECTIVITY	ARROTT, Anthony S.	7/18/00	US	
25563	METHOD AND APPARATUS FOR WRITING DATA STATES TO NON-VOLATILE STORAGE DEVICES	LU, Yong	12/7/99	US	

25598	METHOD AND APPARATUS FOR READING A MAGNETORESISTIVE MEMORY	LU, Yong		7/30/99	US
26025	MAGNETO-RESISTIVE MEMORY WITH SHARE WORDLINE AND SENSE LINE	JOHNSON, William J.		8/14/00	US
26083	MEMORY REDUNDANCY WITH PROGRAMMABLE NON-VOLATILE CONTROL	KIRCHNER, Gary D.		7/18/00	US
26090	MAGNETOC-RESISTIVE MEMORY ARRAY	KATTI, Romney R.		7/18/00	US
26091	PULSED WRITE TECHNIQUES FOR MAGNETO-RESISTIVE MEMORIES	KATTI, Romney R.		8/14/00	US
26310	MAGNETO-RESISTIVE MEMORY HAVING SENSE AMPLIFIER WITH OFFSET CONTROL	DRIES, Michael Frederick		7/18/00	US
17156/25629	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.		4/14/98	US
17156A1	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.		9/14/99	US
17156B1	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.		10/28/99	US
17156US	NON-VOLATILE STORAGE ELEMENT	GADBOIS, Jason B.		4/14/98	US/PCT
25637/26028	PASSIVATED MAGNETO-RESTRICTIVE BIT STRUCTURE AND PASSIVATION METHOD THEREFOR	BERG, Lonny L.		8/14/00	US